

KSD5075

NPN TRIPLE DIFFUSED PLANAR SILICON TRANSISTOR

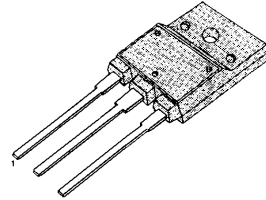
COLOR TV HORIZONTAL OUTPUT APPLICATION (NO Damper Diode)

- High Collector-Base Voltage ($V_{CB0}=1500V$)
- High Speed Switching (tf. max=0.4uS)

ABSOLUTE MIXIMUM RATING

Characteristic	Symbol	Rating	Unit
Collector- Base Voltage	V_{CB0}	1500	V
Collector- Emitter Voltage	V_{CE0}	800	V
Emitter- Base Voltage	V_{EB0}	6	V
Collector Current (DC)	I_C	3.5	A
Collector Current (Pulse)	I_C	10	A
Collector Dissipation ($T_C=25^\circ C$)	P_C	50	W
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{STG}	-50 ~ 150	$^\circ C$

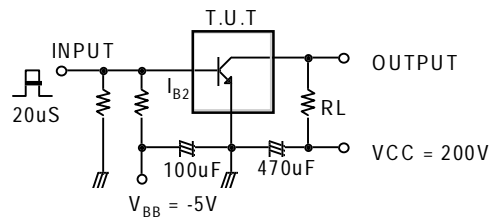
TO-3PF



1. Base 2. Collector 3. Emitter

ELECTRICAL CHARACTERISTICS ($T_C=25^\circ C$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CB0}	$V_{CB} = 800V, I_E = 0$			10	μA
Emitter Cutoff Current	I_{EB0}	$V_{EB} = 5V, I_C = 0$			1	mA
DC Current Gain	h_{FE}	$V_{CE} = 5V, I_C = 0.5A$	8			
Collector Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 2.5A, I_B = 0.8A$			8	V
Base- Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 2.5A, I_B = 0.8A$			1.5	V
Current Gain Bandwidth Product	f_T	$V_{CE} = 10V, I_C = 0.5A$		3		MHz
Fall Time	t_f	$I_C = 3A, I_{B1} = 0.8A$ $I_{B2} = -1.6A, R_L = 66.7\Omega$			0.4	μS



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